

R-C Thermal Model Parameters

DESCRIPTION

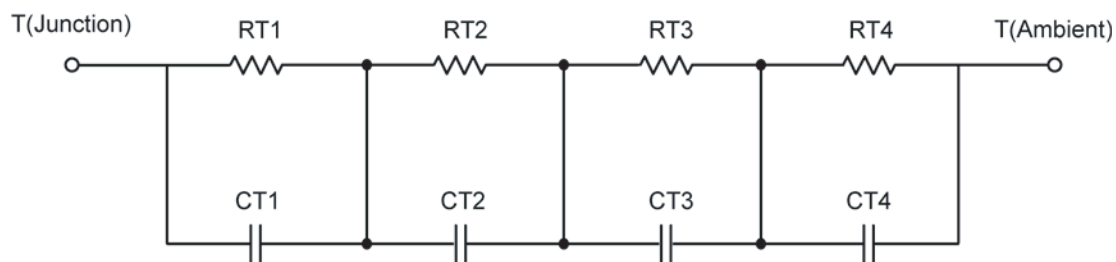
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

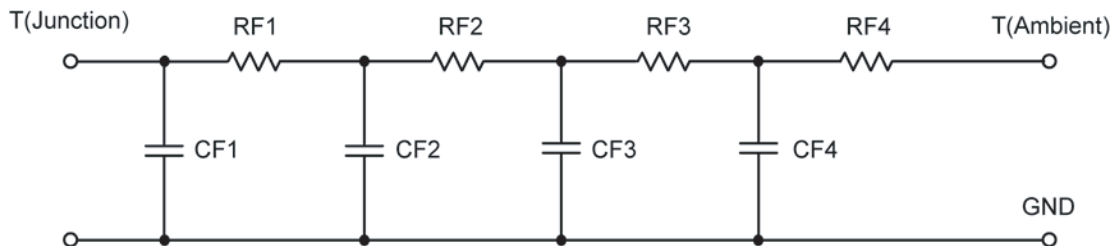
R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	4.6630	N/A	957.8288 m
RT2	30.4017	N/A	4.6741
RT3	26.1463	N/A	9.2794
RT4	22.6225	N/A	6.1811
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	5.7474 m	N/A	1.3107 m
CT2	39.7462 m	N/A	112.4465 m
CT3	1.7481	N/A	189.2448 m
CT4	3.4781	N/A	6.4133 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION

R-C VALUES FOR FILTER CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	2.6371	N/A	4.1688
RF2	32.4430	N/A	6.1387
RF3	28.4228	N/A	6.3994
RF4	20.5668	N/A	4.2738
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	1.0006 m	N/A	2.4342 m
CF2	29.4484 m	N/A	11.8063 m
CF3	885.1865 m	N/A	111.2368 m
CF4	2.0198	N/A	35.5996 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

